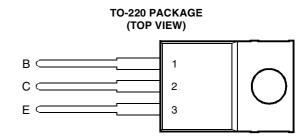


- Designed for Complementary Use with BDX34, BDX34A, BDX34B, BDX34C and BDX34D
- 70 W at 25°C Case Temperature
- 10 A Continuous Collector Current
- Minimum h_{FE} of 750 at 3V, 3 A



Pin 2 is in electrical contact with the mounting base.

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absolute maximum ratings at 25°C case temperature (unless otherwise noted)

RATING	SYMBOL	VALUE	UNIT	
	BDX33		45	
	BDX33A		60	
Collector-base voltage (I _E = 0)	BDX33B	V _{CBO}	80	V
	BDX33C		100	
	BDX33D		120	
	BDX33		45	
	BDX33A		60	
Collector-emitter voltage (I _B = 0)	BDX33B	V _{CEO}	80	V
	BDX33C		100	
	BDX33D		120	
Emitter-base voltage		V _{EBO}	5	V
Continuous collector current	I _C	10	Α	
Continuous base current	I _B	0.3	Α	
Continuous device dissipation at (or below) 25°C case temperature (see Note 1)	P _{tot}	70	W	
Continuous device dissipation at (or below) 25°C free air temperature (see Note	P _{tot}	2	W	
Operating free air temperature range	T _J	-65 to +150	°C	
Storage temperature range	T _{stg}	-65 to +150	°C	
Operating free-air temperature range	T _A	-65 to +150	°C	

NOTES: 1. Derate linearly to 150°C $\,$ case temperature at the rate of 0.56 W/°C.

^{2.} Derate linearly to 150°C free air temperature at the rate of 16 mW/°C.



electrical characteristics at 25°C case temperature (unless otherwise noted)

	PARAMETER		TES1	CONDITIONS		MIN	TYP	MAX	UNIT
					BDX33	45			
	Collector-emitter		I _R = 0		BDX33A	60			
$V_{(BR)CEO}$		$I_{\rm C} = 100 \rm mA$		(see Note 3)	BDX33B	80			V
(511)020	breakdown voltage		5		BDX33C	100			
					BDX33D	120			
		V _{CE} = 30 V	I _B = 0		BDX33			0.5	
		V _{CE} = 30 V	$I_B = 0$		BDX33A			0.5	
		V _{CE} = 40 V	$I_B = 0$		BDX33B			0.5	
		$V_{CE} = 50 \text{ V}$	$I_B = 0$		BDX33C			0.5	
	Collector-emitter	V _{CE} = 60 V	$I_B = 0$		BDX33D			0.5	А
I _{CEO}	cut-off current	V _{CE} = 30 V	$I_B = 0$	$T_C = 100$ °C	BDX33			10	mA
		-	$I_B = 0$	T _C = 100°C	BDX33A			10	
			$I_B = 0$	T _C = 100°C	BDX33B			10	
			$I_B = 0$	T _C = 100°C	BDX33C			10	
		V _{CE} = 60 V	$I_B = 0$	T _C = 100°C	BDX33D			10	
		V _{CB} = 45 V	I _E = 0		BDX33			1	
		V _{CB} = 60 V	I _E = 0		BDX33A			1	
	Collector cut-off current	V _{CB} = 80 V	I _E = 0		BDX33B			1	mA
		V _{CB} = 100 V	$I_E = 0$		BDX33C			1	
		V _{CB} = 120 V	I _E = 0		BDX33D			1	
I _{CBO}			I _E = 0	$T_{\rm C} = 100^{\circ}{\rm C}$	BDX33			5	
		-	I _E = 0		BDX33A			5	
		-	I _E = 0		BDX33B			5	
		~-	I _E = 0		BDX33C			5	
		V _{CB} = 120 V	I _E = 0	T _C = 100°C	BDX33D			5	
I _{EBO}	Emitter cut-off current	V _{EB} = 5 V	I _C = 0					10	mA
		V _{CE} = 3 V	I _C = 4 A		BDX33	750			
	Forward current transfer ratio	V _{CE} = 3 V	$I_C = 4 A$		BDX33A	750			
h_{FE}		V _{CE} = 3 V	$I_C = 3 A$	(see Notes 3 and 4)	BDX33B	750			
		V _{CE} = 3 V	$I_C = 3 A$		BDX33C	750			
		V _{CE} = 3 V	$I_C = 3 A$		BDX33D	750			
	Base-emitter voltage	V _{CE} = 3 V	I _C = 4 A		BDX33			2.5	
		V _{CE} = 3 V	$I_C = 4 A$		BDX33A			2.5	
$V_{BE(on)}$		V _{CE} = 3 V	$I_C = 3 A$	(see Notes 3 and 4)	BDX33B			2.5	V
(3)		V _{CE} = 3 V	$I_C = 3 A$		BDX33C			2.5	
		V _{CE} = 3 V	$I_C = 3 A$		BDX33D			2.5	
	Collector-emitter saturation voltage	I _B = 8 mA	I _C = 4 A		BDX33			2.5	
		I _B = 8 mA	$I_C = 4 A$		BDX33A			2.5	
$V_{CE(sat)}$		$I_B = 6 \text{ mA}$	$I_C = 3 A$	(see Notes 3 and 4)	BDX33B			2.5	V
()		$I_B = 6 \text{ mA}$	$I_C = 3 A$		BDX33C			2.5	
		I _B = 6 mA	$I_C = 3 A$		BDX33D			2.5	
V _{EC}	Parallel diode forward voltage	I _E = 8 A	I _B = 0					4	V

NOTES: 3. These parameters must be measured using pulse techniques, $t_0 = 300 \mu s$, duty cycle $\leq 2\%$.

^{4.} These parameters must be measured using voltage-sensing contacts, separate from the current carrying contacts.



thermal characteristics

PARAMETER			TYP	MAX	UNIT
$R_{\theta JC}$	Junction to case thermal resistance			1.78	°C/W
$R_{\theta JA}$	Junction to free air thermal resistance			62.5	°C/W

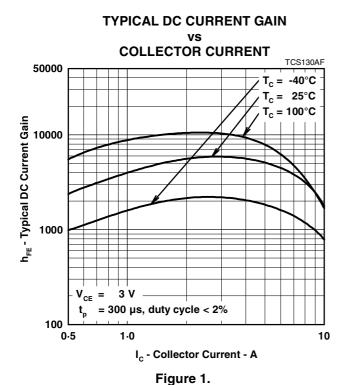
resistive-load-switching characteristics at 25°C case temperature

	PARAMETER	TEST CONDITIONS †			MIN	TYP	MAX	UNIT
t _{on}	Turn-on time	I _C = 3 A	$I_{B(on)} = 12 \text{ mA}$	$I_{B(off)} = -12 \text{ mA}$		1		μs
t _{off}	Turn-off time	$V_{BE(off)} = -3.5 \text{ V}$	$R_L = 10 \Omega$	t_p = 20 μ s, dc \leq 2%		5		μs

[†] Voltage and current values shown are nominal; exact values vary slightly with transistor parameters.



TYPICAL CHARACTERISTICS



COLLECTOR-EMITTER SATURATION VOLTAGE

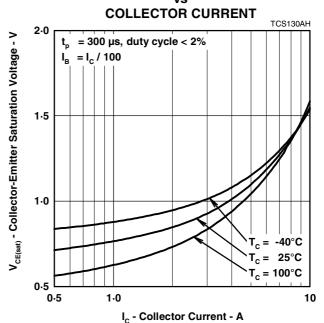
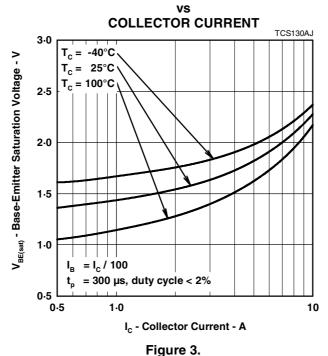


Figure 2.

BASE-EMITTER SATURATION VOLTAGE



PRODUCT INFORMATION

THERMAL INFORMATION

MAXIMUM POWER DISSIPATION

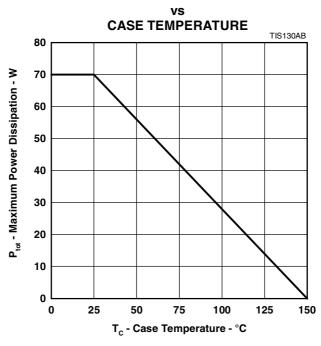


Figure 4.